

### 20V N-Channel Enhancement Mode MOSFET

Voltage 20 V Current 4.0A

#### **Features**

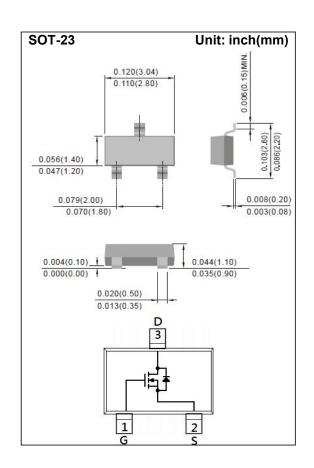
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_{D}@4.0A<56m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}$ @2.5V,  $I_{D}$ @2.8A<68m $\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@1.8V$ ,  $I_{D}@1.5A<95m\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.

#### **Mechanical Data**

• Case: SOT-23 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0003 ounces, 0.0084 grams



# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

| PARAME   | SYMBOL               | LIMIT            | UNITS   |        |  |
|--|----------------------|------------------|---------|--------|--|
| Drain-Source Voltage                                     | V <sub>DS</sub>      | 20               | V       |        |  |
| Gate-Source Voltage                                      | V <sub>GS</sub>      | <u>+</u> 12      |         |        |  |
| Continuous Drain Current                                 |                      | I <sub>D</sub>   | 4.0     | А      |  |
| Pulsed Drain Current                                     |                      | I <sub>DM</sub>  | 16.4    |        |  |
| Power Dissipation  | T <sub>a</sub> =25°C | P <sub>D</sub>   | 1.25    | W      |  |
|  | Derate above 25°C    |                  | 10      | mW/ °C |  |
| Operating Junction and Storage Temperature Range         |                      | $T_{J}, T_{STG}$ | -55~150 | °C     |  |
| Typical Thermal Resistance  Junction to Ambient (Note 3) |                      | $R_{\theta JA}$  | 100     | °C/W   |  |



# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| PARAMETER                        | SYMBOL              | TEST CONDITION  | MIN. | TYP. | MAX.         | UNITS |
|----------------------------------|---------------------|---|------|------|--------------|-------|
| Static                           |                     |   |      |      |              |       |
| Drain-Source Breakdown Voltage   | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250uA                                      | 20   | -    | -            | V     |
| Gate Threshold Voltage           | $V_{GS(th)}$        | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA                        | 0.4  | 0.66 | 1.2          |       |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.0A                                     | -    | 41   | 56           | mΩ    |
|                                  |                     | V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.8A                                     | -    | 50   | 68           |       |
|                                  |                     | V <sub>GS</sub> =1.8V, I <sub>D</sub> =1.5A                                     | -    | 66   | 95           |       |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> =20V, V <sub>GS</sub> =0V                                       | -    | -    | 1            | uA    |
| Gate-Source Leakage Current      | $I_{GSS}$           | V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V                             | -    | -    | <u>+</u> 100 | nA    |
| Dynamic (Note 5)                 |                     |   |      |      |              |       |
| Total Gate Charge                | $Q_g$               | 101111111111111111111111111111111111111   | -    | 4.6  | -            | nC    |
| Gate-Source Charge               | $Q_gs$              | V <sub>DS</sub> =10V, I <sub>D</sub> =4.0A,<br>V <sub>GS</sub> =4.5V (Note 1,2) | -    | 0.8  | -            |       |
| Gate-Drain Charge                | $Q_{gd}$            |   | -    | 1    | -            |       |
| Input Capacitance                | Ciss                | V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,                                      | -    | 350  | -            | pF    |
| Output Capacitance               | Coss                |   | -    | 40   | -            |       |
| Reverse Transfer Capacitance     | Crss                | f=1MHZ  | -    | 29   | -            |       |
| Turn-On Delay Time               | td <sub>(on)</sub>  | \/ 40\/ L 40A   | -    | 4    | -            | ns    |
| Turn-On Rise Time                | tr                  | $V_{DD}$ =10V, $I_{D}$ =4.0A, $V_{GS}$ =4.5V,                                   | -    | 47   | -            |       |
| Turn-Off Delay Time              | td <sub>(off)</sub> |   | -    | 18   | -            |       |
| Turn-Off Fall Time               | tf                  | $R_G=6\Omega$ (Note 1,2)  | -    | 10   | -            |       |
| Drain-Source Diode               |                     |   |      |      | •            | •     |
| Maximum Continuous Drain-Source  |                     |   | -    | -    | 1.5          | А     |
| Diode Forward Current            | Is                  |   |      |      |              |       |
| Diode Forward Voltage            | $V_{SD}$            | I <sub>S</sub> =1A, V <sub>GS</sub> =0V   | -    | 0.75 | 1.2          | V     |

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Reja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.



### TYPICAL CHARACTERISTIC CURVES

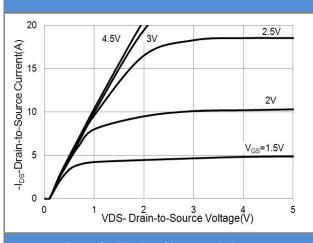
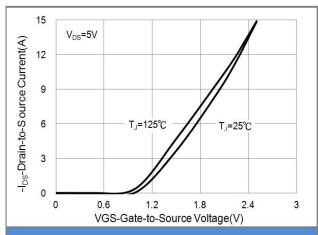


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

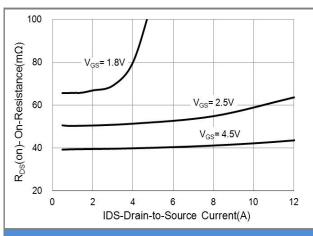


Fig.3 On-Resistance vs. Drain Current

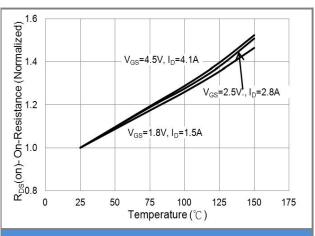


Fig.4 On-Resistance vs. Junction temperature

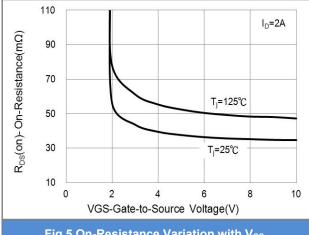


Fig.5 On-Resistance Variation with V<sub>GS</sub>

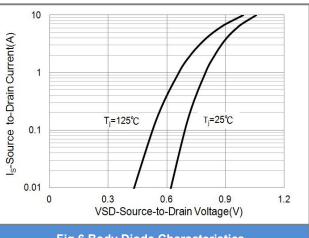


Fig.6 Body Diode Characteristics



### TYPICAL CHARACTERISTIC CURVES

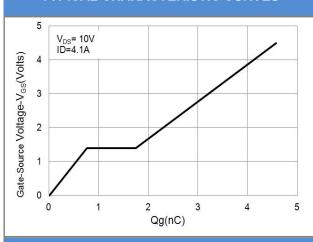


Fig.7 Gate-Charge Characteristics

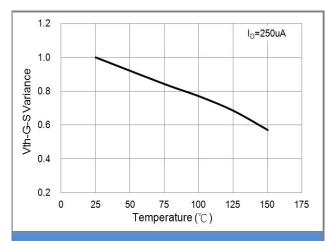


Fig.8 Threshold Voltage Variation with Temperature

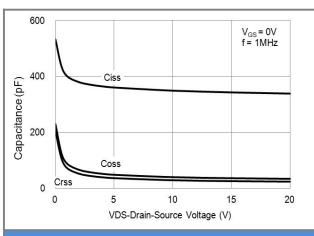


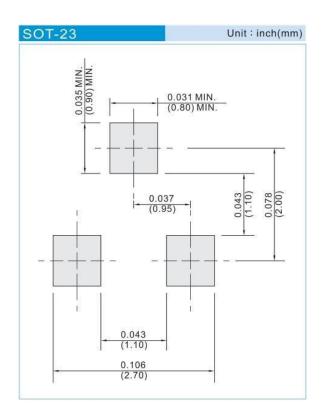
Fig.9 Capacitance vs. Drain-Source Voltage



# **Part No Packing Code Version**

| Part No Packing Code | Package Type | Packing Type     | Marking | Version      |
|----------------------|--------------|------------------|---------|--------------|
| CSM2302S23           | SOT-23       | 3K pcs / 7" reel |         | Halogen free |

# **Mounting Pad Layout**





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